

ABSTRACT OF THE DISCLOSURE

A semiconductor laser device has a silicon oxide film formed so as to be in contact with at least one end of a semiconductor laser crystal as an end face protection film for a semiconductor laser element. For example, the
5 semiconductor laser device has a silicon oxide film formed so as to be in contact with a main emission face side of a laser chip. Such a silicon oxide film preferably has an index of refraction not smaller than 1.6. Another film may be formed outside the silicon oxide film. The silicon oxide film is preferably formed with resistance heating vapor deposition. Thus, a
10 semiconductor laser device which is provided with an end face protection film, and can avoid COD level lowering and attain high reliability of a laser element, as well as a method of manufacturing the same can be provided.